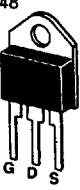


Power MOSFETS (cont'd)

ECG Type	Description and Application	Transconductance gfs μmhos	Drain to Source Breakdown Voltage BV _{DSS}	Gate to Source Breakdown Voltage BV _{GS}	Continuous Drain Current I _D Amps	Gate to Source Threshold Voltage V _{GS} (th)	Drain to Source Resistance r _{DS} (on) Ohms	Input Cap C _{iss} pf	Device Dissipation @T _C =25° C P _D Watts	Package
										Case/Fig./Basing
ECG2387 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	800 Min	±30 Max*	4	4 Max	3 Max	1250 Max	125 Max	TO-220 Fig. T41 
						td(off) = 150 ns, td(on) = 25 ns, tf = 60 ns, tr = 40 ns				
ECG2399 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	1000 Min	±30 Max*	3	4 Max	5 Max	1250 Max	125 Max	
						td(off) = 130 ns, td(on) = 10 ns, tf = 40 ns, tr = 25 ns				
ECG2940 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	60 Min	±20 Max	13	4 Max	.09 Max	850 Max	30 Max	TO-220J Fig. T41-I 
						td(off) = 70 ns, td(on) = 40 ns, tf = 60 ns, tr = 60 ns				
ECG2941 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	16 Min	60 Min	±20 Max*	32	4 Max	.02 Max	2900 Max	45 Max	
						td(off) = 200 ns, td(on) = 90 ns, tf = 220 ns, tr = 700 ns				
ECG2942 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	100 Min	±20 Max*	10	4 Max	.16 Max	1100 Max	35 Max	
						td(off) = 70 ns, td(on) = 60 ns, tf = 30 ns, tr = 60 ns				
ECG2943 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	10 Min	100 Min	±20 Max*	18	4 Max	.06 Max	2000 Max	40 Max	
						td(off) = 140 ns, td(on) = 40 ns, tf = 110 ns, tr = 70 ns				
ECG2944 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	200 Min	±20 Max*	10	4 Max	.18 Max	1600 Max	45 Max	
						td(off) = 140 ns, td(on) = 90 ns, tf = 60 ns, tr = 60 ns				
ECG2945 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	400 Min	±20 Max*	6	4 Max	.55 Max	1600 Max	45 Max	
						td(off) = 100 ns, td(on) = 50 ns, tf = 50 ns, tr = 150 ns				
ECG2946 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3.5 Min	500 Min	±20 Max*	5	4 Max	.85 Max	2000 Max	45 Max	
						td(off) = 120 ns, td(on) = 50 ns, tf = 30 ns, tr = 20ns				
ECG2947 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	600 Min	±20 max*	4	4 Max	1.25 Max	2000 Max	45 Max	
						td(off) = 170 ns, td(on) = 80 ns, tf = 50 ns, tr = 50 ns				
ECG2393 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	500 Min	±20 Max*	9	4 Max	.7 Max	1900 Max	150 Max	TO-3P (TO-218) Fig. T48 
						td(off) = 170 ns, td(on) = 40 ns, tf = 40 ns, tr = 60 ns				
ECG2394 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	9 Min	500 Min	±20 Max*	14	4 Max	.4 Max	3000 Max	180 Max	
						td(off) = 150 ns, td(on) = 35 ns, tf = 70 ns, tr = 50 ns				
ECG2378 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	1 Min	900 Min	±20 Max	5	4 Max	4 Max	950 Typ	150 Max	TO-3PJ • Fig. T48-1 
						td(off) = 80 ns, td(on) = 20 ns, tf = 20 ns, tr = 40 ns				
ECG2377 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	2 Min	900 Min	±30 Max*	8	3.5 Max	1.5 Max	1300 Typ	150 Max	• TO-247 Alt. Case Fig T48-4 
						td(off) = 200 ns, td(on) = 90 ns, tf = 220 ns, tr = 700 ns				

* Warning - Exceeding BV_{GS} maximum will result in permanent damage to the gate region oxide layer.
 ▲ Refer to MOSFET Handling Precautions - Page 1 - 34

Package Outlines - See Page 1-91